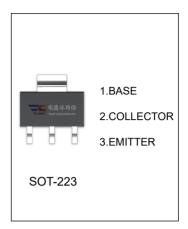


B772 TRANSISTOR (PNP)

FEATURES

- Power Dissipation:1.25W
- Low Collector-emitter Saturation Voltage



MAXIMUM RATINGS(Ta=25 ℃ unless otherwise not)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage -6		V
Ic	Collector Current -Continuous	-3	Α
Pc	Collector Dissipation	1.25	W
R _{ΘJA}	Thermal Resistance from Junction to Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=-100μA, I _E =0	Ic=-100μA, I _E =0 -40			V
Collector-emitter breakdown voltage	V(BR)CEO	I _C =-10mA, I _B =0 -30				V
Emitter-base breakdown voltage	V(BR)EBO	I _E =-100 μA, I _C =0	100 μA, I _C =0 -6			V
Collector cut-off current	I _{CBO}	V _{CB} =-40 V, I _E =0	V, I _E =0		-1	μA
Collector cut-off current	ctor cut-off current I _{CEO} V _{CE} =-30 V I _B =0				-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -6V,I _C =0			-1	μA
DC current gain	h _{FE (1)}	V _{CE} =-2V,I _C =-1A	60		400	
De current gam	h _{FE (2)}	V _{CE} =-2V,I _C =-100mA	32			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 2A,I _B =-0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE} (sat) I _C = 2A,I _B =-0.2A				-1.5	V
Transition frequency	f _⊤	V _{CE} =-5V,I _C =-0.1A f=10MHz	50			MHz

CLASSIFICATION of hfE(1)

Rank	R	0	Υ	GR
Range	60-120	100-200	160-320	200-400



